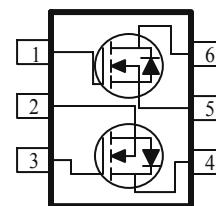
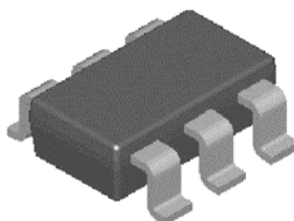


Dual N-Channel Logic Level MOSFET

These miniature surface mount MOSFETs utilize High Cell Density process. Low  $r_{DS(on)}$  assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are logic switch control, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low  $r_{DS(on)}$  Provides Higher Efficiency and Extends Battery Life
- Miniature TSOP-6 Surface Mount Package Saves Board Space
- Very fast switching
- Gate to Source Zener Diode ESD Protect

PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ (OHM)	$I_D$ (A)
25	0.45 @ $V_{GS} = 4.5\text{ V}$	0.5
	0.63 @ $V_{GS} = 2.5\text{ V}$	0.2



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)			
Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	25	V
Gate-Source Voltage	$V_{GS}$	8	
Continuous Drain Current <sup>a</sup>	$I_D$	$T_A=25^\circ\text{C}$	A
		$T_A=70^\circ\text{C}$	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	2	
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	$\pm 0.3$	A
Power Dissipation <sup>a</sup>	$P_D$	$T_A=25^\circ\text{C}$	W
		$T_A=70^\circ\text{C}$	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>a</sup>	$R_{THJA}$	t $\leq$ 5 sec	$^\circ\text{C/W}$
		Steady-State	

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	25			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	0.67	0.85	1.5	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			100	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	uA
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$			10	
On-State Drain Current <sup>A</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 2.5\text{ V}$	0.5			A
Drain-Source On-Resistance <sup>A</sup>	$r_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 0.5\text{ A}$		0.33	0.45	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 0.5\text{ A}, T_J = 55^\circ\text{C}$		0.36	0.49	
		$V_{GS} = 2.5\text{ V}, I_D = 0.2\text{ A}$		0.45	0.63	
Forward Transconductance <sup>A</sup>	$g_{fs}$	$V_{DS} = 5\text{ V}, I_D = 0.5\text{ A}$		1.5		S
Diode Forward Voltage	$V_{SD}$	$I_S = 0.5\text{ A}, V_{GS} = 0\text{ V}$		0.85	1.20	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 5\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 0.5\text{ A}$		1.7	2.3	nC
Gate-Source Charge	$Q_{gs}$			0.38	0.72	
Gate-Drain Charge	$Q_{gd}$			0.47	0.87	
<b>Switching</b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 6\text{ V}, I_D = 0.5\text{ A},$ $V_{GEN} = 4.5\text{ V}, R_G = 50\text{ }\Omega$		6.5	13	ns
Rise Time	$t_r$			11	19	
Turn-Off Delay Time	$t_{d(off)}$			13	24	
Fall-Time	$t_f$			3	7	

## Notes

- Pulse test:  $PW \leq 300\mu\text{s}$  duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.

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### Typical Electrical Characteristics

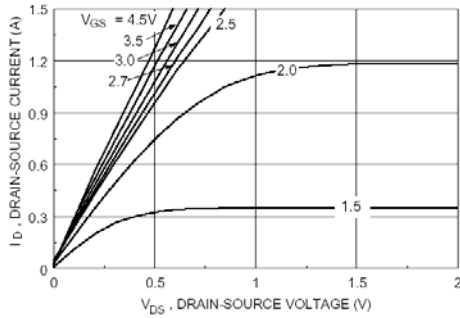


Figure 1. On-Region Characteristics

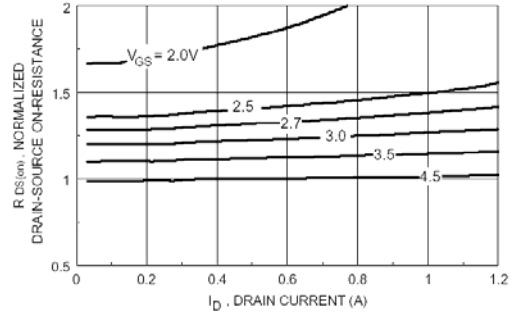


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

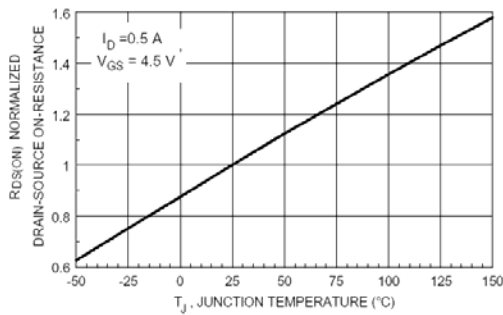


Figure 3. On-Resistance Variation with Temperature

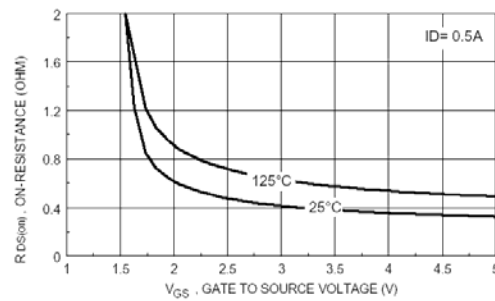


Figure 4. On-Resistance Variation with Gate to Source Voltage

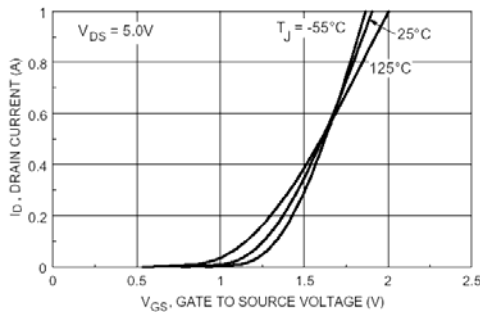


Figure 5. Transfer Characteristics

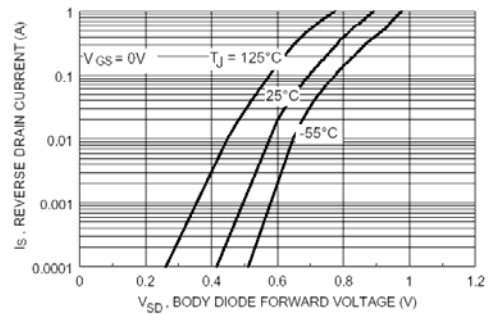


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

### Typical Electrical Characteristics

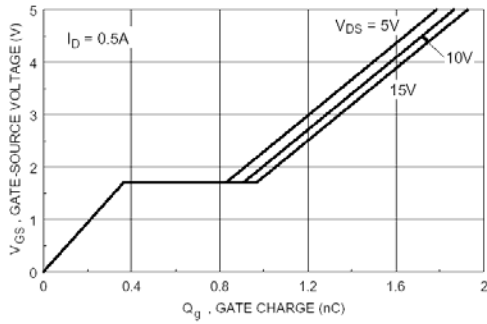


Figure 7. Gate Charge Characteristics.

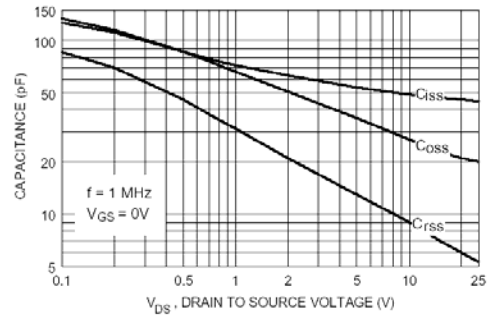


Figure 8. Capacitance Characteristics.

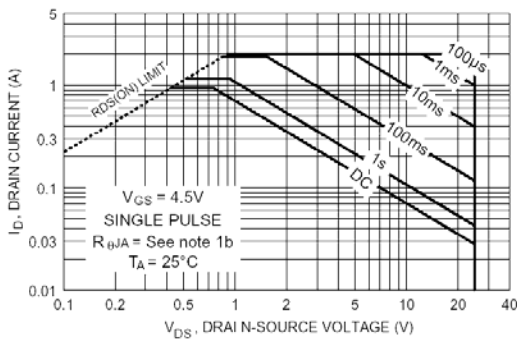


Figure 9. Maximum Safe Operating Area

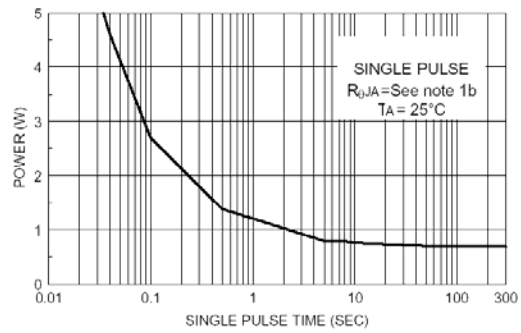


Figure 10. Single Pulse Maximum Power Dissipation

### Normalized Thermal Transient Junction to Ambient

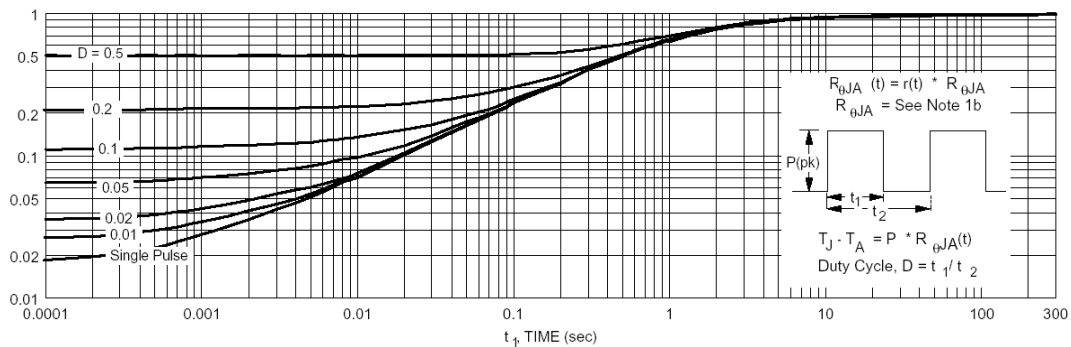
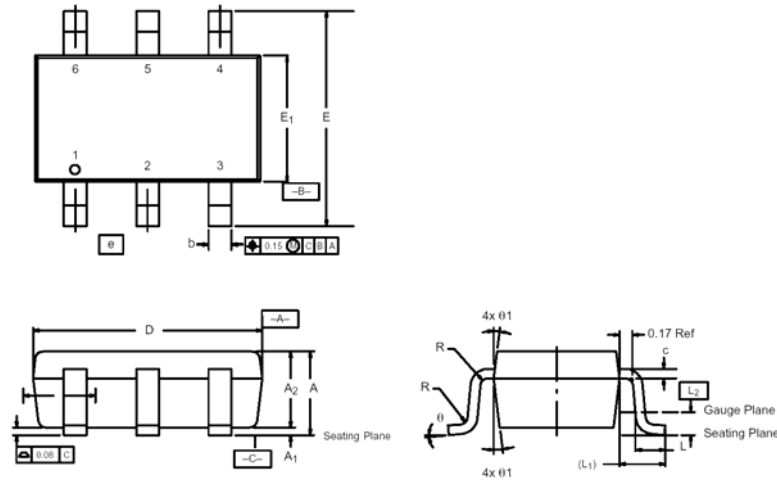


Figure 11. Transient Thermal Response Curve

Package Information

TSOP-6: 6LEAD



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	—	1.10	0.036	—	0.043
A <sub>1</sub>	0.01	—	0.10	0.0004	—	0.004
A <sub>2</sub>	0.84	—	1.00	0.033	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067
e	1.00 BSC			0.0394 BSC		
L	0.35	—	0.50	0.014	—	0.020
L <sub>1</sub>	0.60 Ref			0.024 Ref		
L <sub>2</sub>	0.25 BSC			0.010 BSC		
R	0.10	—	—	0.004	—	—
θ	0°	4°	8°	0°	4°	8°
θ <sub>1</sub>	7° Nom			7° Nom		